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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/770,520	02/04/2004	Tomohiro Saito	05225.0259	1739
22852 75	90 07/13/2005		EXAMINER	
FINNEGAN, HENDERSON, FARABOW, GARRETT & DUNNER			EVERHART, CARIDAD	
LLP 901 NEW YORK AVENUE, NW			ART UNIT	PAPER NUMBER
	WASHINGTON, DC 20001-4413			
			DATE MAILED: 07/13/2009	5

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
Office Action 2	10/770,520	SAITO ET AL.
Office Action Summary	Examiner	Art Unit
	Caridad M. Everhart	2891
The MAILING DATE of this communic Period for Reply	cation appears on the cover sheet with t	he correspondence address
A SHORTENED STATUTORY PERIOD FO THE MAILING DATE OF THIS COMMUNIC - Extensions of time may be available under the provisions o after SIX (6) MONTHS from the mailing date of this commu - If the period for reply specified above is less than thirty (30) - If NO period for reply is specified above, the maximum state - Failure to reply within the set or extended period for reply w Any reply received by the Office later than three months aft earned patent term adjustment. See 37 CFR 1.704(b).	CATION. f 37 CFR 1.136(a). In no event, however, may a reply nication. days, a reply within the statutory minimum of thirty (30 utory period will apply and will expire SIX (6) MONTHS rill, by statute, cause the application to become ABAND	be timely filed  O) days will be considered timely.  From the mailing date of this communication.  DONED (35 U.S.C. § 133).
Status		
1) Responsive to communication(s) filed	I on <i>21 April 2005</i> .	
2a)⊠ This action is <b>FINAL</b> .	b) ☐ This action is non-final.	•
· · · · · · · · · · · · · · · · · · ·	or allowance except for formal matters e under <i>Ex parte Quayle</i> , 1935 C.D. 1	•
Disposition of Claims		
4) Claim(s) 1-18,20 and 22 is/are pendir 4a) Of the above claim(s) is/are 5) Claim(s) 3-5/ As/are allowed. 6) Claim(s) // 2/ is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction	e withdrawn from consideration.	
Application Papers		
9) The specification is objected to by the 10) The drawing(s) filed on is/are:		the Eveniner
	ion to the drawing(s) be held in abeyance.	
	the correction is required if the drawing(s) is	• •
11) The oath or declaration is objected to		
Priority under 35 U.S.C. § 119		
_	locuments have been received. locuments have been received in Appli f the priority documents have been rec	ication No
* See the attached detailed Office action	for a list of the certified copies not rec	eived.
L	•	
Attachment(s)	<b></b> □	(070 440)
Notice of References Cited (PTO-892)     Notice of Draftsperson's Patent Drawing Review (PT)	4) ∐ Interview Sumr O-948) Paper No(s)/M	mary (PTO-413) ail Date
3) Note that the statement (S) (PTO-1449 or P Paper No(s)/Mail Date 2/4/04		mal Patent Application (PTO-152)

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Applicant's arguments with respect to claims, have been considered but are moot in view of the new ground(s) of rejection.

Applicant has amended to include the limitation "primarily visible light", and applicant's arguments are based upon this new limitation.

## Claim Rejections - 35 USC § 103

The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.

Claims 1,2,6-8,10-11,13,15, and 17 are rejected under 35 U.S.C. 103(a) as being unpatentable over Byun, et al. (US 5,744,398) in view of Komatsu (US 5,654,242) and further in view of Weiner(US 5,569,624) and further in view of Nakamura, et al (US 2005/0142818A1).

Byun, et al disclose the steps of forming a gate dielectric, depositing a tungsten silicide layer, doping the silicide layer, heat treating the silicide layer, patterning the silicide to form a gate, and forming source and drain regions by implanting, using the gate as a mask(col. 1, lines 62-67; col. 2, lines 1-5 and 10-20; and col. 3,lines 18-24).

Byun, et al is silent with respect to the control of the work function and with respect to the use or irradiating for the heat treatment and with respect to visible light.

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Komatsu discloses the control of the work function of a tungsten silicide gate in a CMOS device by implantation and heat treatment of the silicide gate(col. 1,lines 17-21; col. 11, lines 63-67; col. 12, lines 66-67; col. 13, lines 1-14 and 51-55).

Weiner teaches the equivalence of furnace heating with rapid thermal anneal in the heating of an implanted layer(col. 5, lines 65-67 and col. 6, lines 1-3). Weiner also teaches the use of laser anneal(col. 4, lines 45-53).

Nakamura et al teaches that YAG laser is a visible light laser(paragraph 0173) and teaches YAG laser annealing(paragraph 0173).

It would have been obvious to one of ordinary skill in the art at the time of the invention that the work function was controlled in the process taught by Byun, et al because Komatsu teaches that the implantation and heating steps control the work function of a tungsten silicide gate. It would have been obvious to one of ordinary skill in the art at the time of the invention to have used irradiation in the method taught by Byun, et al because Weiner teaches the equivalence of furnace heat treatment such as used by Byun, et al and irradiation such as rapid thermal treatment, which is irradiation using a lamp, which is an incoherent source or radiation. It would also have been obvious to one of ordinary skill in the art at the time of the invention to have used coherent radiation such as laser radiation as taught by Weiner in the process taught by Byun, et al because Weiner teaches that this method prevents the dopant from being driven into the substrate from the silicide(col. 4, lines 48-53). In addition, because Weiner teaches YAG laser (col. 4, lines 65-67), it would have been obvious to one of

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ordinary skill in the art at the time of the invention that this encompasses visible light because Nakamura et al teaches that the YAG laser is a visible light laser.

## Allowable Subject Matter

Claims 3-5,9,12,14,16, and 18 are allowed.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Caridad M. Everhart whose telephone number is 571-272-1892. The examiner can normally be reached on Monday through Fridays 7:30-4:00.

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a). Applicant's amendment necessitated the new grounds of rejection.

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on 571-272-1907. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

CARIDAD EVERHARY PRIMARY EXAMINED

C. Euchas

C. Everhart 1-19-2005